# MSKSEMI















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# Broduct data sheet



#### **SOT-89**

1. BASE



3. EMITTER



#### **FEATURES**

- Low  $V_{CE(sat)}$ ,  $V_{CE(sat)}$ =0.15V(typical).( $I_C/I_B$ =500mA/50mA)
- Complements to 2SB1132

### MAXIMUM RATINGS (T<sub>A</sub>=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	32	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current -Continuous	1	Α
Pc	Collector power dissipation	500	mW
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =50μA, I <sub>E</sub> =0	40			٧
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	32			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =50μA, I <sub>C</sub> =0	5			٧
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =20V, I <sub>E</sub> =0			0.5	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			0.5	μΑ
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =3V, I <sub>C</sub> =100mA	82		390	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =0.5A, I <sub>B</sub> =50mA			0.4	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =50mA, f=100MHz		150		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		15		pF

#### CLASSIFICATION OF hFE

Rank	Р	Q	R
Range	82-180	120-270	180-390
Marking	DAP	DAQ	DAR



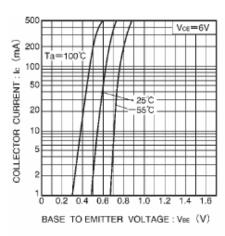


Fig.1 Grounded emitter propagation characteristics

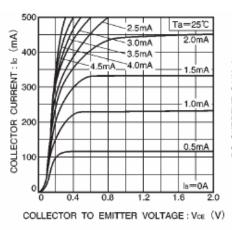


Fig.2 Grounded emitter output characteristics

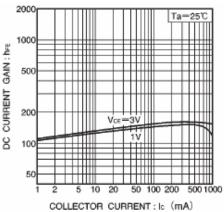


Fig.3 DC current gain vs. collector current (I)

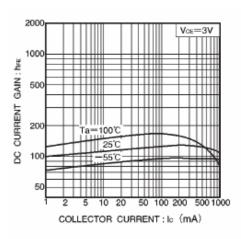


Fig.4 DC current gain vs. collector current (II)

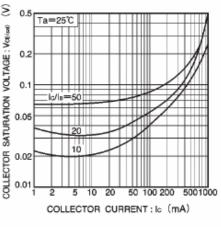


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

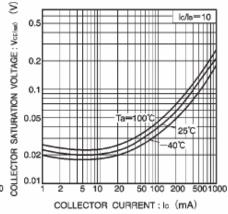


Fig.6 Collector-emitter saturation voltage vs. collector current ( I )

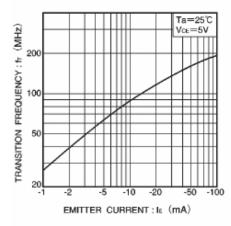


Fig.7 Gain bandwidth product vs. emitter current

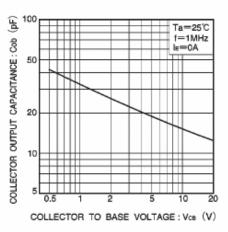


Fig.8 Collector output capacitance vs. collector-base voltage

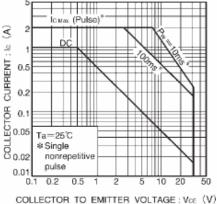


Fig.9 Safe operating area (2SD1664)



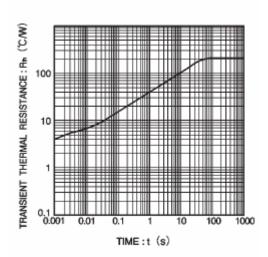
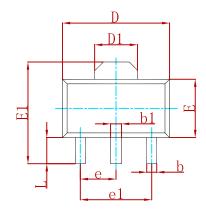
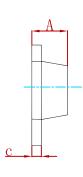


Fig.10 Transient thermal resistance (2SD1664)



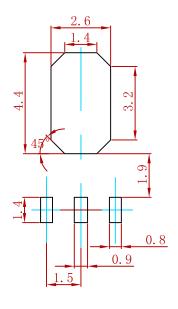
#### **PACKAGE MECHANICAL DATA**





Symbol	Dimensions In Millimeters		Dimensions In Inches	
Зушвої	Min	Max	Min	Max
Α	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
С	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550	REF.	0.061	REF.
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
е	1.500 TYP.		0.060 TYP.	
e1	3.000	) TYP.	0.118	TYP.
L	0.900	1.200	0.035	0.047

# **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
2SD1164	SOT-89	1000



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